Large-Signal Modeling and Study of Power Saturation Mechanisms in Heterojunction Bipolar Transistors

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M.Y. Frankel and D. Pavlidis. "Large-Signal Modeling and Study of Power Saturation Mechanisms in Heterojunction Bipolar Transistors." 1991 MTT-S International Microwave Symposium Digest 91.1 (1991 Vol. I [MWSYM]): 127-130.

A harmonic balance based large-signal model of the heterojunction bipolar transistor suitable for microwave circuit design and simulation has been developed. The excellent agreement between modeled and measured power characteristics, including the saturation behavior, validates its accuracy. The model has been used to investigate the device power saturation mechanisms.

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